NUS2045MN, NUS3045MN

Overvoltage Protection IC with Integrated MOSFET

These devices represent a new level of safety and integration by combining the NCP345 overvoltage protection circuit (OVP) with a 20 V P−channel power MOSFET (NUS2045MN) or with a 30 V P−channel power MOSFET (NUS3045MN). They are specifically designed to protect sensitive electronic circuitry from overvoltage transients and power supply faults. During such hazardous events, the IC quickly disconnects the input supply from the load, thus protecting the load before any damage can occur.

The OVP ICs are optimized for applications using an external AC−DC adapter or a car accessory charger to power a portable product or recharge its internal batteries. They have a nominal overvoltage threshold of 6.85 V which makes them ideal for single cell Li−Ion as well as 3/4 cell NiCD/NiMH applications.

Features

- OvervoltageTurn−Off Time of Less Than 1.0 μs
- Accurate Voltage Threshold of 6.85 V, Nominal
- Undervoltage Lockout Protection; 2.8 V, Nominal
- Control Input Compatible with 1.8 V Logic Levels
- −20 V or −30 V Integrated P−Channel Power MOSFET
- Low $R_{DS(on)}$ = 70 mΩ @ −4.5 V for NUS2045MN
  Low $R_{DS(on)}$ = 68 mΩ @ −4.5 V for NUS3045MN
- Low Profile 3.3 x 3.3 mm DFN Package Suitable for Portable Applications
- Maximum Solder Reflow temperature @ 235°C for MNT1 suffix and 260°C for MNT1G suffix
- Pb−Free Packages are Available

Benefits

- Provide Battery Protection
- Integrated Solution Offers Cost and Space Savings
- Integrated Solution Improves System Reliability

Applications

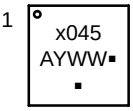
- Portable Computers and PDAs
- Cell Phones and Handheld Products
- Digital Cameras

ON Semiconductor®

http://onsemi.com

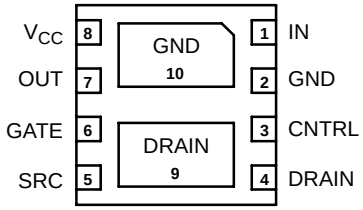
DFN8
CASE 506AL

MARKING DIAGRAM



x045 = Device Code
x = 2 or 3
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb−Free Package
(Note: Microdot may be in either location)

PIN ASSIGNMENT



(Bottom View)

ORDERING INFORMATION

Device	Package	Shipping†
NUS2045MNT1	DFN8	3000 Tape & Reel
NUS2045MNT1G	DFN8 (Pb−Free)	3000 Tape & Reel
NUS3045MNT1	DFN8	3000 Tape & Reel
NUS3045MNT1G	DFN8 (Pb−Free)	3000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

January, 2006 − Rev. 2

Publication Order Number:
NUS2045MN/D

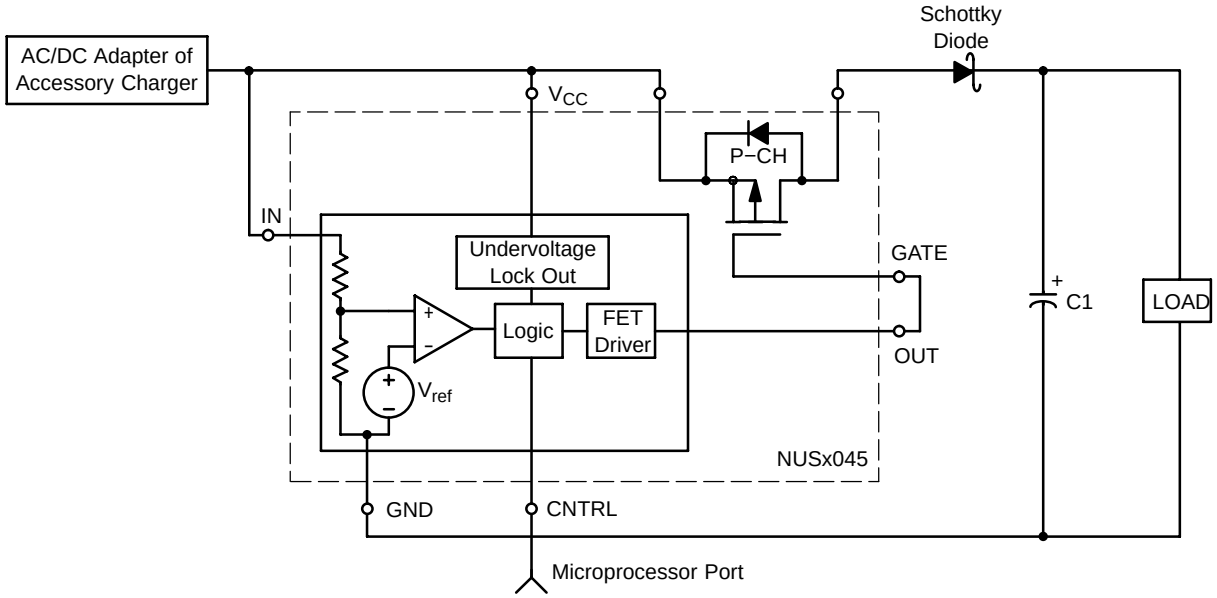


Figure 1. Simplified Schematic

PIN FUNCTION DESCRIPTIONS

Pin #	Symbol	Pin Description
1	IN	This pin senses an external voltage point. If the voltage on this input rises above the overvoltage threshold (V_{TH}), the OUT pin will be driven to within 1.0 V of V_{CC}, thus disconnecting the FET. The nominal threshold level is 6.85 V and this threshold level can be increased with the addition of an external resistor between IN and V_{CC}.
2, 10	GND	Circuit Ground
3	CNTRL	This logic signal is used to control the state of OUT and turn−on/off the P−channel MOSFET. A logic High results in the OUT signal being driven to within 1.0 V of V_{CC} which disconnects the FET. If this pin is not used, the input should be connected to ground.
4, 9	DRAIN	Drain pin of the power MOSFET
5	SRC	Source pin of the power MOSFET
6	GATE	Gate pin of the power MOSFET
7	OUT	This signal drives the gate of a P−channel MOSFET. It is controlled by the voltage level on IN or the logic state of the CNTRL input. When an overvoltage event is detected, the OUT pin is driven to within 1.0 V of V_{CC} in less than 1.0 _sec provided that gate and stray capacitance is less than 12 nF.
8	V_{CC}	Positive Voltage supply. If V_{CC} falls below 2.8 V (nom), the OUT pin will be driven to within 1.0 V of V_{CC}, thus disconnecting the P−channel FET.

OVERVOLTAGE PROTECTION CIRCUIT TRUTH TABLE

IN	CNTRL	OUT
$<V_{th}$	L	GND
$<V_{th}$	H	V_{CC}
$>V_{th}$	L	V_{CC}
$>V_{th}$	H	V_{CC}

MAXIMUM RATINGS (T_A = 25°C unless otherwise stated)

Rating	Pin	Symbol	Min	Max	Unit
OUT Voltage to GND	7	V_O	−0.3	30	V
Input and CNTRL Pin Voltage to GND	1 3	V_{input} V_{CNTRL}	−0.3 −0.3	30 13	V
V_{CC} Maximum Range	8	$V_{CC(max)}$	−0.3	30	V
Maximum Power Dissipation (Note 1)	−	P_D	−	1.0	W
Thermal Resistance Junction−to−Air (Note 1) OVP IC P−Channel FET	−	$R_{\theta JA}$	−	108.6 104.3	°C/W
Junction Temperature	−	T_J	−	150	°C
Operating Ambient Temperature	−	T_A	−40	85	°C
V_{CNTRL} Operating Voltage	3	−	0	5.0	V
Storage Temperature Range	−	T_{stg}	−65	150	°C
ESD Performance (HBM) (Note 2)	1,2,3,7,8,10	−	2.5	−	kV
Drain−to−Source Voltage NUS2045MN NUS3045MN		V_{DSS}		 −20 −30	V
Gate−to−Source Voltage NUS2045MN NUS3045MN		V_{GS}	 −8 −20	 8 20	V
Continuous Drain Current, Steady State, T_A = 25°C (Note 1) NUS2045MN NUS3045MN		I_D		 −0.6 −1.0	A

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Surface−mounted on FR4 board using 1 inch sq pad size (Cu area = 1.127 in sq [1 oz] including traces).
2. Human body model (HBM): MIL STD 883C Method 3015−7, (R = 1500 Ω, C = 100 pF, F = 3 pulses delay 1 s).

ELECTRICAL CHARACTERISTICS (T_A= 25°C, Vcc = 6.0 V, unless otherwise specified)

Characteristic	Symbol	Pin	Min	Typ	Max	Unit
V_{CC} Operating Voltage Range	$V_{CC(opt)}$	8	3.0	4.8	25	V
Supply Current (I_{CC} + I_{Input}; V_{CC} = 6.0 V Steady State)	−	1, 8	−	0.75	1.0	mA
Input Threshold (V_{Input} connected to V_{CC}; V_{Input} increasing)	V_{Th}	1	6.65	6.85	7.08	V
Input Hysteresis (V_{Input} connected to V_{CC}; V_{Input} decreasing)	V_{Hyst}	1	50	100	200	mV
Input Impedance (Input = V_{Th})	R_{in}	1	70	150	−	kΩ
CNTRL Voltage High	V_{ih}	3	1.5	−	−	V
CNTRL Voltage Low	V_{il}	3	−	−	0.5	V
CNTRL Current High (V_{ih} = 5.0 V)	I_{ih}	3	−	95	200	μA
CNTRL Current Low (V_{il} = 0.5 V)	I_{il}	3	−	10	20	μA
Undervoltage Lockout (V_{CC} decreasing)	V_{Lock}	3	2.5	2.8	3.0	V
Output Sink Current (V_{CC} < V_{Th}, V_{OUT} = 1.0 V)	I_{Sink}	7	10	33	50	μA
Output Voltage High (V_{CC} = V_{in} = 8.0 V; I_{Source} = 10 mA) Output Voltage High (V_{CC} = V_{in} = 8.0 V; I_{Source} = 0.25 mA) Output Voltage High (V_{CC} = V_{in} = 8.0 V; I_{Source} = 0 mA)	V_{oh}	7	V_{CC}−1.0 V_{CC}−0.25 V_{CC}−0.1	−	−	V
Output Voltage Low (Input < 6.5 V; I_{Sink} = 0 mA; V_{CC} = 6.0 V, CNTRL = 0 V)	V_{ol}	7	−	−	0.1	V
Turn ON Delay − Input (Note 3) (V_{Input} connected to V_{CC}; V_{Input} step down signal from 8.0 to 6.0 V; measured to 50% point of OUT)*	$T_{ON\ IN}$	7	−	−	10	μs
Turn OFF Delay − Input (V_{Input} connected to V_{CC}; V_{Input} step up signal from 6.0 to 8.0 V; C_L = 12 nF Output > V_{CC} − 1.0 V)	$T_{OFF\ IN}$	7	−	0.5	1.0	μs
Turn ON Delay − CNTRL (CNTRL step down signal from 2.0 to 0.5 V; measured to 50% point of OUT) (Note 3)	$T_{ON\ CT}$	7	−	−	10	μs
Turn OFF Delay − CNTRL (CNTRL step up signal from 0.5 to 2.0 V; C_L = 12 nF Output > V_{CC} −1.0 V)	$T_{OFF\ CT}$	7	−	1.0	2.0	μs

3. Guaranteed by design.

P−CHANNEL MOSFET

Parameter		Symbol	Min	Typ	Max	Units
Drain to Source On Resistance		$R_{DS(on)}$				mΩ
V_{GS} = −4.5 V, I_D = 600 mA	NUS2045MN			71	95	
V_{GS} = −4.5 V, I_D = 1.0 A	NUS2045MN			71	95	
V_{GS} = −4.5 V, I_D = 600 mA	NUS3045MN			66	110	
V_{GS} = −4.5 V, I_D = 1.0 A	NUS3045MN			66	110	
Zero Gate Voltage Drain Current		I_{DSS}				μA
V_{GS} = 0 V, V_{DS} = −16 V	NUS2045MN				−1.0	
V_{GS} = 0 V, V_{DS} = −24 V	NUS3045MN				−1.0	
Turn On Delay (Note 4)		t_{on}				ns
V_{GS} = −4.5 V	NUS2045MN			7.5		
V_{GS} = −4.5 V	NUS3045MN			11		
Turn Off Delay (Note 4)		t_{off}				ns
V_{GS} = −4.5 V	NUS2045MN			30.2		
V_{GS} = −4.5 V	NUS3045MN			28		
Input Capacitance (Note 3)		C_{in}				pF
V_{GS} = 0 V, f = 1.0 MHz, V_{DS} = −10 V	NUS2045MN				675	
V_{GS} = 0 V, f = 1.0 MHz, V_{DS} = −15 V	NUS3045MN				750	
Gate to Source Leakage Current		I_{GSS}				nA
V_{GS} = ±8.0 V, V_{DS} = 0 V	NUS2045MN			±10		
V_{GS} = ±20 V, V_{DS} = 0 V	NUS3045MN			±10		
Drain to Source Breakdown Voltage		$V_{(BR)DSS}$				V
V_{GS} = 0 V, I_D = −250 μA	NUS2045MN		20			
	NUS3045MN		30			
Gate Threshold Voltage		$V_{(GS)th}$				V
V_{GS} = V_{DS}, I_D = −250 μA	NUS2045MN		−1.2		−0.4	
	NUS3045MN		−3.0		−1.0	

4. Switching characteristics are independent of operating junction temperature.

TYPICAL PERFORMANCE CURVES

(T_A= 25°C, unless otherwise specified)

OVERVOLTAGE PROTECTION IC

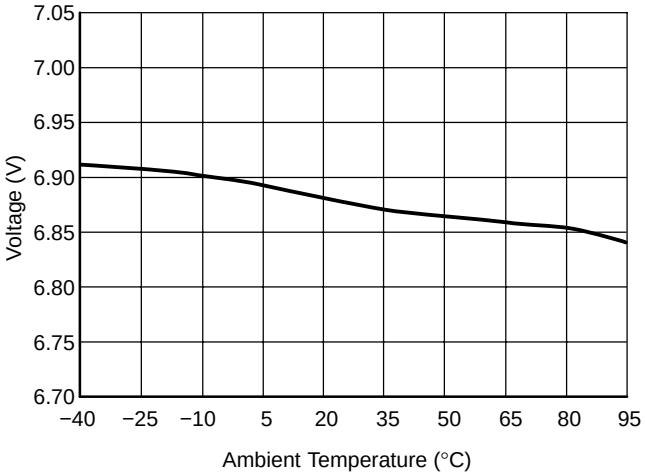


Figure 2. Typical V_{th} Threshold Variation vs. Temperature

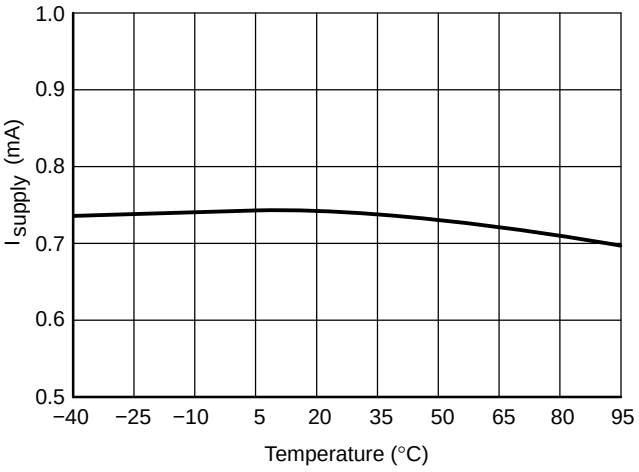


Figure 3. Typical Supply Current vs. Temperature I_{cc} + I_{in}, V_{CC} = 6 V

TYPICAL PERFORMANCE CURVES

(T_A= 25°C, unless otherwise specified)

30 V, P−CHANNEL MOSFET

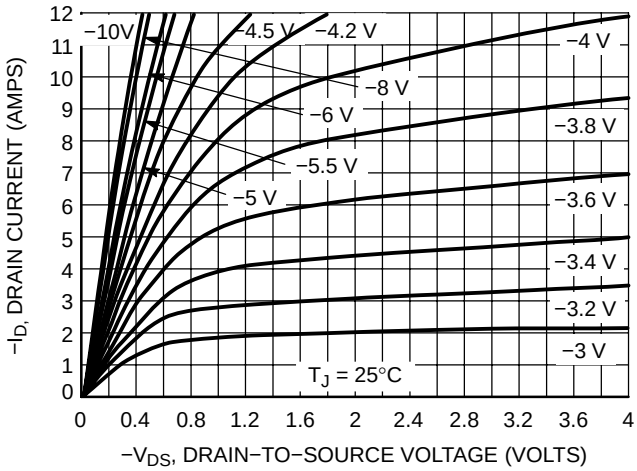


Figure 4. On−Region Characteristics

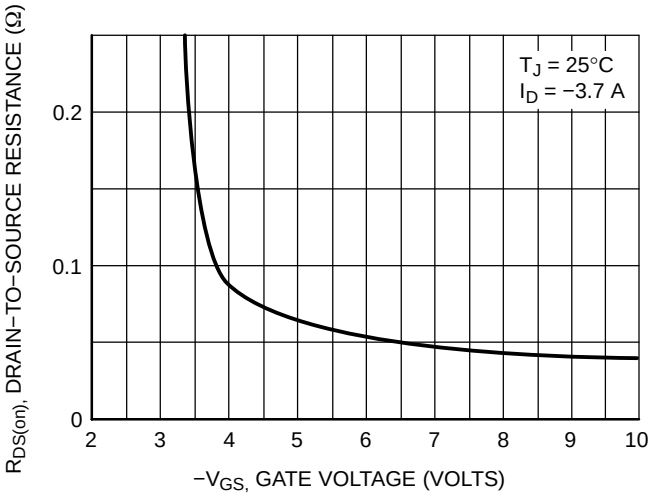


Figure 5. On−Resistance vs. Gate−to−Source Voltage

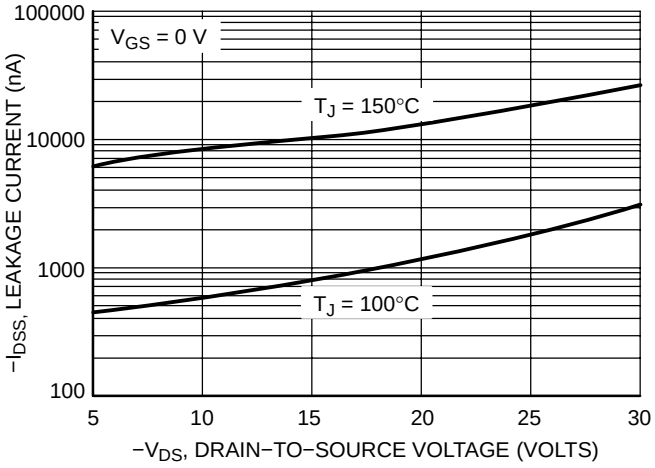


Figure 6. Drain−to−Source Leakage Current vs. Voltage

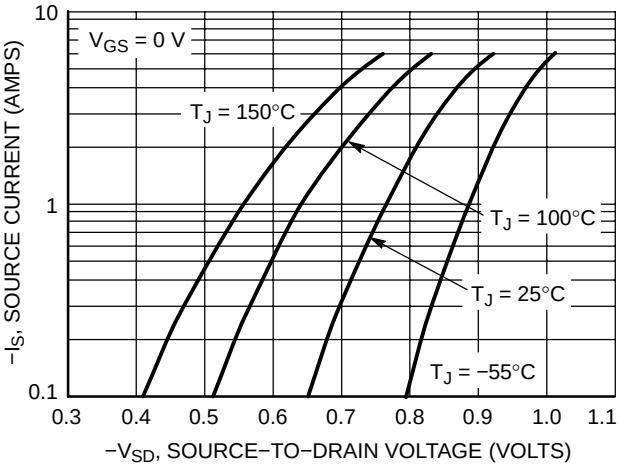


Figure 7. Diode Forward Voltage vs. Current

TYPICAL PERFORMANCE CURVES

(T_A= 25°C, unless otherwise specified)

20 V, P−CHANNEL MOSFET

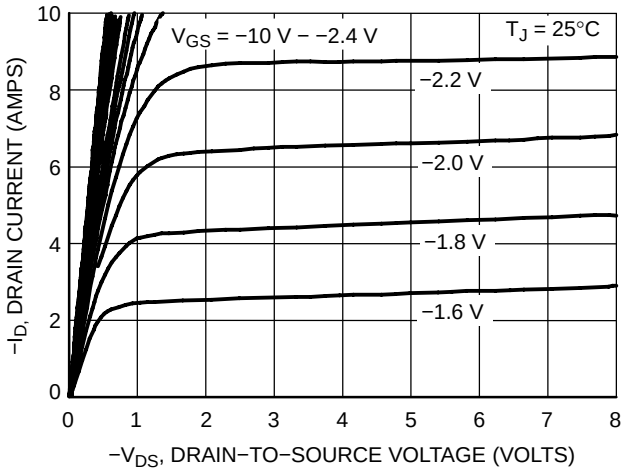


Figure 8. On−Region Characteristics

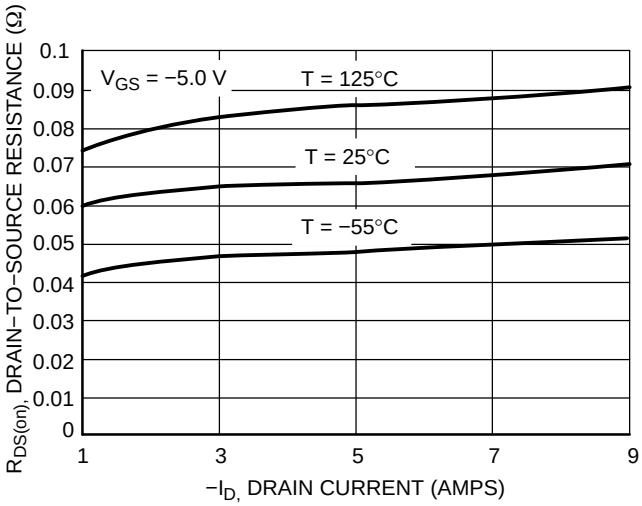


Figure 9. On−Resistance vs. Drain Current and Temperature

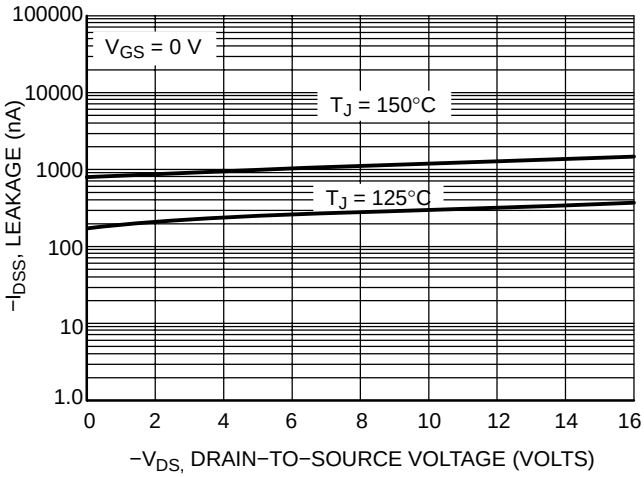


Figure 10. Drain−to−Source Leakage Current vs. Voltage

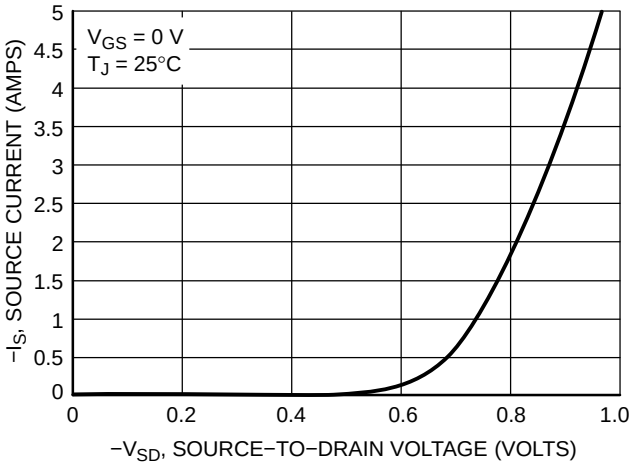


Figure 11. Diode Forward Voltage vs. Current

TYPICAL APPLICATION CIRCUITS & OPERATION WAVEFORMS

(T_A= 25°C, unless otherwise specified)

20 V, P−CHANNEL MOSFET

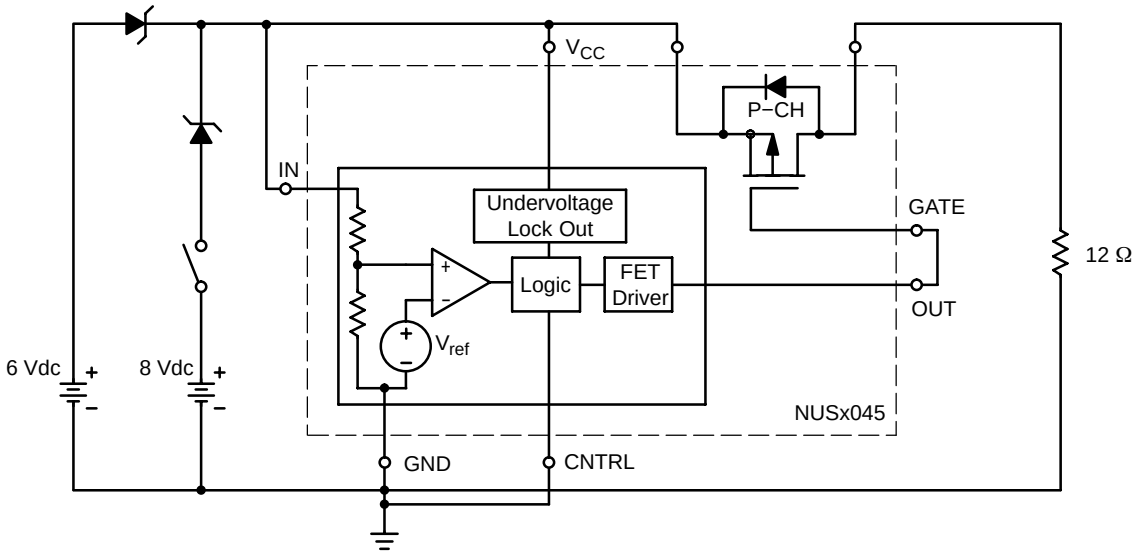


Figure 12. Test Circuit for $T_{ON\ IN}$ and $T_{OFF\ IN}$

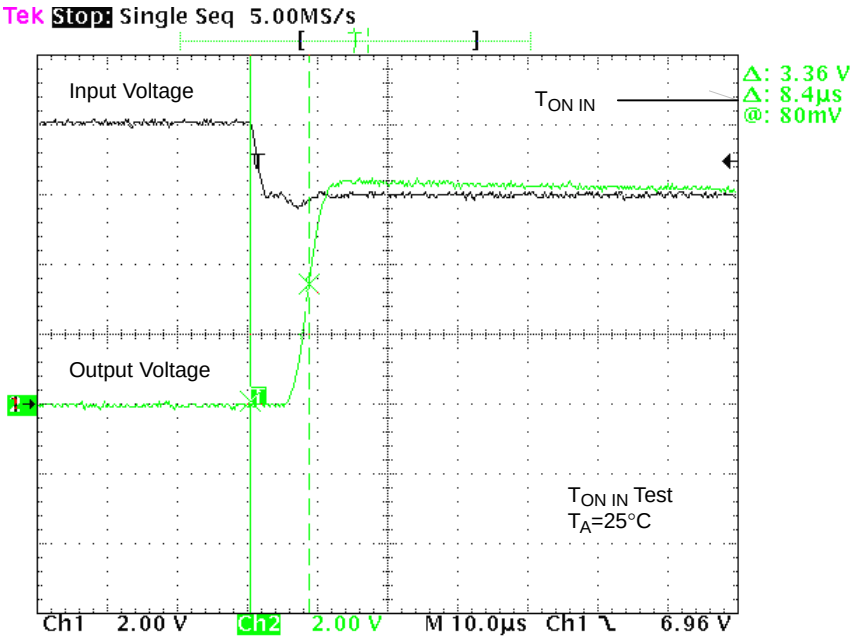


Figure 13. $T_{ON\ IN}$ Waveforms

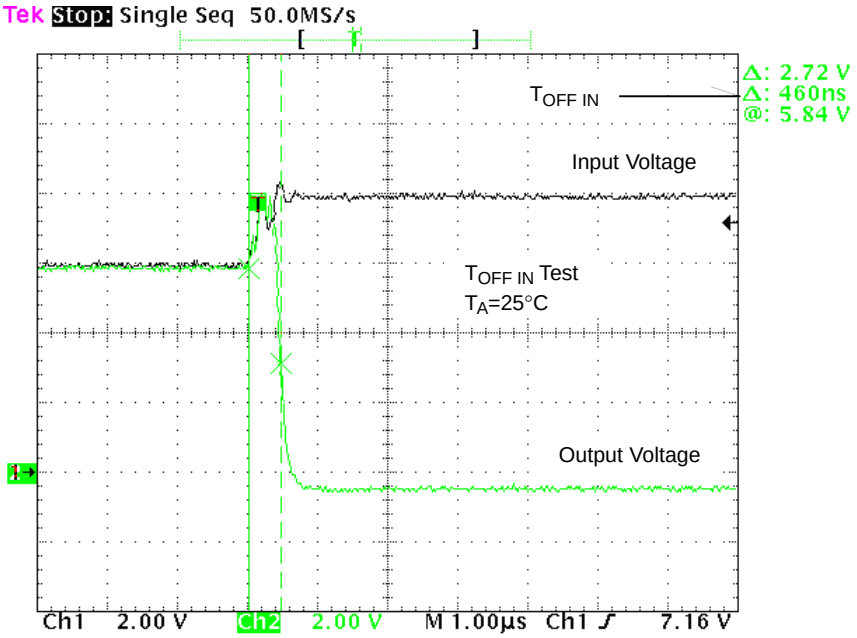


Figure 14. $T_{OFF\ IN}$ Waveforms

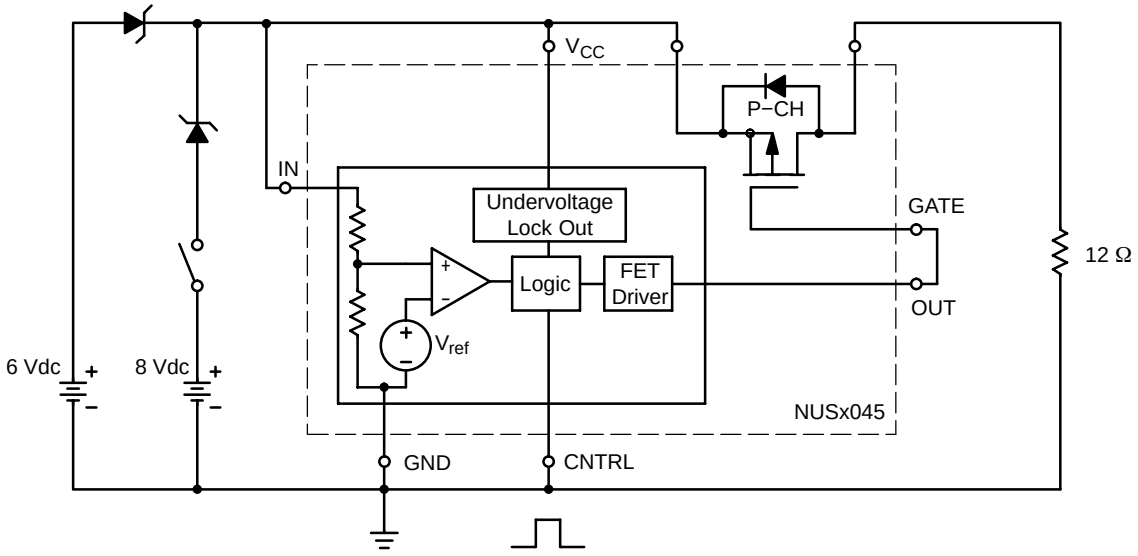


Figure 15. Test Circuit for $T_{ON\ CT}$ and $T_{OFF\ CT}$

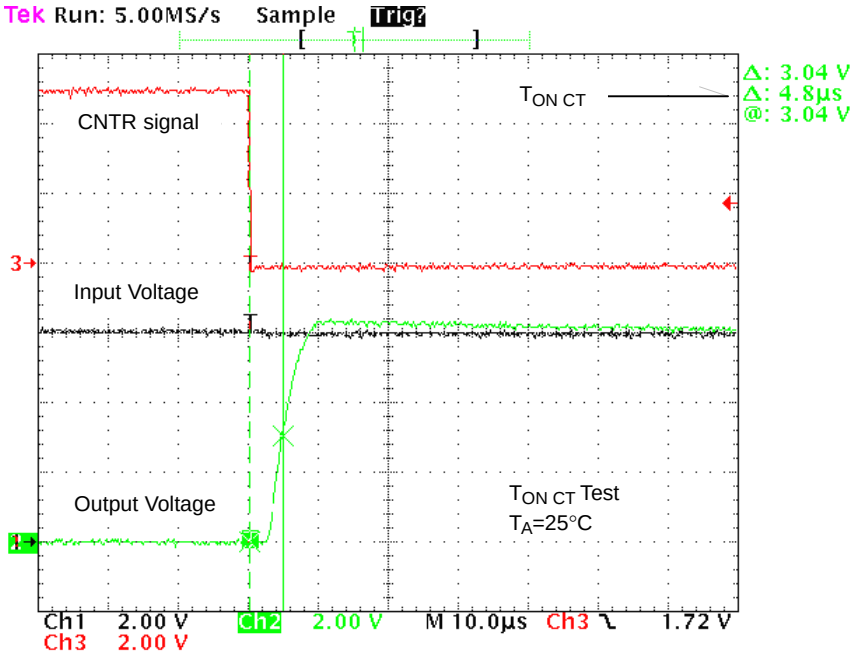


Figure 16. $T_{ON\ CT}$ Waveforms

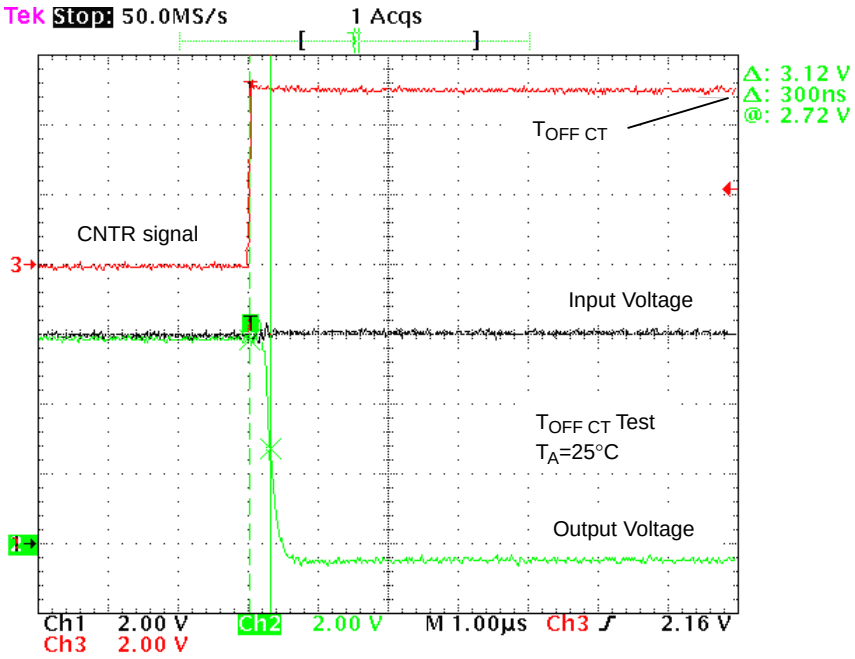
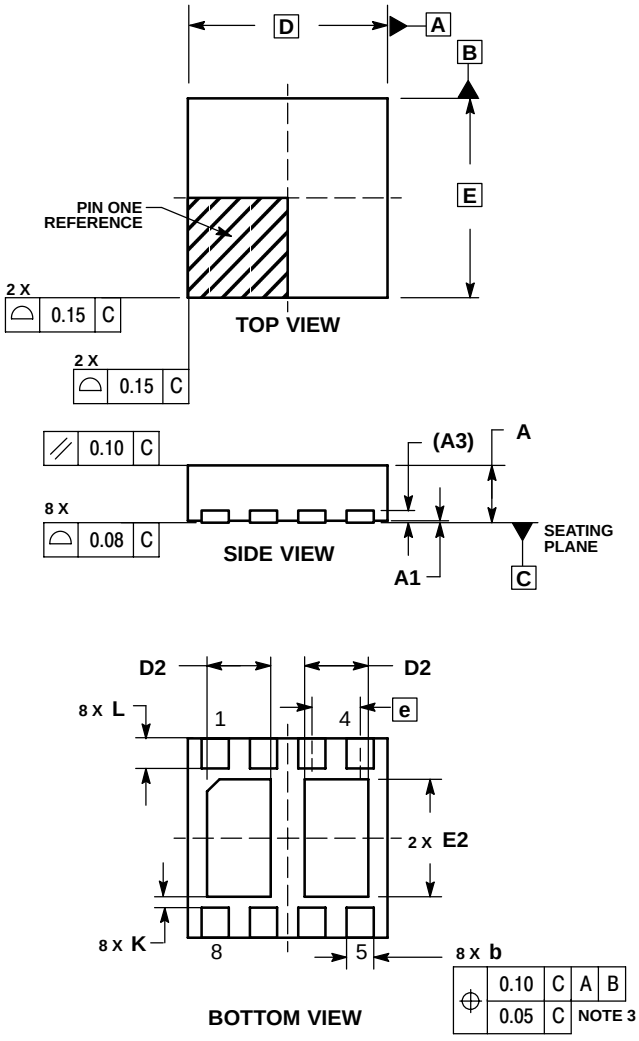


Figure 17. $T_{OFF\ CT}$ Waveforms

PACKAGE DIMENSIONS

DFN8
CASE 506AL−01
ISSUE O



NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.25 AND 0.30mm.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

	MILLIMETERS		
DIM	MIN	NOM	MAX
A	0.80	0.90	1.00
A1	0.00	0.03	0.05
A3		0.20 REF	
b	0.35	0.40	0.45
D		3.30 BSC	
D2	0.95	1.05	1.15
E		3.30 BSC	
E2	1.80	1.90	2.00
e		0.80 BSC	
K	0.21	−−−	−−−
L	0.30	0.40	0.50

PUBLICATION ORDERING INFORMATION

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